# BLC10G27XS-551AVT

# Power LDMOS transistor

**AMPLEON** 

Rev. 1 — 20 September 2019

Product data sheet

## 1. Product profile

#### 1.1 General description

550 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 2620 MHz to 2690 MHz.

#### Table 1. Typical performance

Typical RF performance at  $T_{case} = 25$  °C in an asymmetrical Doherty demo circuit.  $V_{DS} = 32$  V;  $I_{Dq} = 1000$  mA (main);  $V_{GS(amp)peak} = 0.85$  V, unless otherwise specified.

| Test signal      | f            | V <sub>DS</sub> | P <sub>L(AV)</sub> | G <sub>p</sub> | η <sub>D</sub> | ACPR                 |
|------------------|--------------|-----------------|--------------------|----------------|----------------|----------------------|
|                  | (MHz)        | (V)             | (W)                | (dB)           | (%)            | (dBc)                |
| 1-carrier W-CDMA | 2620 to 2690 | 32              | 91                 | 13.5           | 46             | -31.3 <sup>[1]</sup> |

<sup>[1]</sup> Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

#### 1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 2620 MHz to 2690 MHz frequency range

# 2. Pinning information

Table 2. Pinning

| Pin | Description             |     | Simplified outline | Graphic symbol     |
|-----|-------------------------|-----|--------------------|--------------------|
| 1   | drain2 (peak)           |     |                    | 0.7                |
| 2   | drain1 (main)           |     | 7 2 1 6            | 2, 7               |
| 3   | gate1 (main)            |     | 5                  |                    |
| 4   | gate2 (peak)            |     | 3 4                | 3——5               |
| 5   | source                  | [1] |                    | 4—                 |
| 6   | video decoupling (peak) |     |                    | <b>'</b> Ь         |
| 7   | video decoupling (main) |     |                    | 1, 6<br>aaa-014884 |

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

| Type number       | Packaç           | Package   |           |  |  |  |
|-------------------|------------------|---|-----------|--|--|--|
|                   | Name Description |   | Version   |  |  |  |
| BLC10G27XS-551AVT | -                | air cavity plastic earless flanged package; 6 leads | SOT1258-4 |  |  |  |

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                   | Parameter                          | Conditions    | Min | Max  | Unit |
|--------------------------|------------------------------------|---------------|-----|------|------|
| V <sub>DS</sub>          | drain-source voltage               |               | -   | 65   | V    |
| V <sub>GS(amp)main</sub> | main amplifier gate-source voltage |               | -6  | +9   | V    |
| V <sub>GS(amp)peak</sub> | peak amplifier gate-source voltage |               | -6  | +9   | V    |
| T <sub>stg</sub>         | storage temperature                |               | -65 | +150 | °C   |
| Tj                       | junction temperature               | [1]           | -   | 225  | °C   |
| T <sub>case</sub>        | case temperature                   | operating [1] | -40 | +125 | °C   |

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

### 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol               | Parameter                                | Conditions   | Тур  | Unit |
|----------------------|--|--|------|------|
| R <sub>th(j-c)</sub> | thermal resistance from junction to case | V <sub>DS</sub> = 32 V; I <sub>Dq</sub> = 1000 mA (main);<br>V <sub>GS(amp)peak</sub> = 0.885 V; T <sub>case</sub> = 80 °C |      |      |
|                      |  | P <sub>L</sub> = 87 W  | 0.24 | k/W  |
|                      |  | P <sub>L</sub> = 110 W   | 0.22 | k/W  |

BLC10G27XS-551AVT

#### 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C unless otherwise specified.

| Symbol               | Parameter                        | Conditions   | Min      | Тур  | Max | Unit |
|----------------------|----------------------------------|--|----------|------|-----|------|
| Main dev             | rice                             |  | <b>-</b> |      | 1   |      |
| V <sub>(BR)DSS</sub> | drain-source breakdown voltage   | $V_{GS} = 0 \text{ V}; I_D = 1.8 \text{ mA}$                       | 65       | -    | -   | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage    | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 180 mA                    | 1.6      | 2.0  | 2.4 | V    |
| $V_{GSq}$            | gate-source quiescent voltage    | V <sub>DS</sub> = 32 V; I <sub>D</sub> = 1000 mA                   | -        | 2.2  | -   | V    |
| I <sub>DSS</sub>     | drain leakage current            | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V                      | -        | -    | 2.8 | μΑ   |
| I <sub>DSX</sub>     | drain cut-off current            | $V_{GS} = V_{GS(th)} + 2.37 \text{ V};$<br>$V_{DS} = 10 \text{ V}$ | -        | 34   | -   | A    |
| I <sub>GSS</sub>     | gate leakage current             | V <sub>GS</sub> = 9 V; V <sub>DS</sub> = 0 V                       | -        | -    | 280 | nA   |
| 9 <sub>fs</sub>      | forward transconductance         | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 9.0 A                     | -        | 20.5 | -   | S    |
| R <sub>DS(on)</sub>  | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 2.37 \text{ V};$<br>$I_D = 6.3 \text{ A}$   | -        | 72   | 108 | mΩ   |
| Peak dev             | rice                             |  |          |      |     |      |
| V <sub>(BR)DSS</sub> | drain-source breakdown voltage   | $V_{GS} = 0 \text{ V}; I_D = 3.8 \text{ mA}$                       | 65       | -    | -   | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage    | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 380 mA                    | 1.6      | 2.0  | 2.4 | V    |
| $V_{GSq}$            | gate-source quiescent voltage    | V <sub>DS</sub> = 32 V; I <sub>D</sub> = 1900 mA                   | -        | 2.2  | -   | V    |
| I <sub>DSS</sub>     | drain leakage current            | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V                      | -        | -    | 2.8 | μΑ   |
| I <sub>DSX</sub>     | drain cut-off current            | $V_{GS} = V_{GS(th)} + 2.37 \text{ V};$<br>$V_{DS} = 10 \text{ V}$ | -        | 57   | -   | A    |
| I <sub>GSS</sub>     | gate leakage current             | V <sub>GS</sub> = 9 V; V <sub>DS</sub> = 0 V                       | -        | -    | 280 | nA   |
| g <sub>fs</sub>      | forward transconductance         | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 19.0 A                    | -        | 39.0 | -   | S    |
| R <sub>DS(on)</sub>  | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $I_D = 13.3 \text{ A}$     | -        | 37   | 62  | mΩ   |

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH;  $f_1$  = 2622.5 MHz;  $f_2$  = 2687.5 MHz; RF performance at  $V_{DS}$  = 32 V;  $I_{Dq}$  = 1000 mA (main);  $V_{GS(amp)peak}$  = 0.9 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2620 MHz to 2690 MHz.

| Symbol     | Parameter                    | Conditions                | Min | Тур | Max | Unit |
|------------|------------------------------|---------------------------|-----|-----|-----|------|
| Gp         | power gain                   | P <sub>L(AV)</sub> = 91 W | 12  | 13  | -   | dB   |
| RLin       | input return loss            | P <sub>L(AV)</sub> = 91 W | -   | -14 | -10 | dB   |
| $\eta_{D}$ | drain efficiency             | P <sub>L(AV)</sub> = 91 W | 41  | 45  | -   | %    |
| ACPR       | adjacent channel power ratio | P <sub>L(AV)</sub> = 91 W | -   | -29 | -24 | dBc  |

#### Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f = 2687.5 MHz; RF performance at  $V_{DS} = 32$  V;  $I_{Dq} = 1000$  mA (main);  $V_{GS(amp)peak} = 0.9$  V;  $T_{case} = 25$  °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at a frequency of 2690 MHz.

| Symbol     | Parameter                    | Conditions                 | Min | Тур | Max | Unit |
|------------|------------------------------|----------------------------|-----|-----|-----|------|
| PARO       | output peak-to-average ratio | P <sub>L(AV)</sub> = 145 W | 5.9 | 6.4 | -   | dB   |
| $P_{L(M)}$ | peak output power            | P <sub>L(AV)</sub> = 145 W | 553 | 628 | -   | W    |

BLC10G27XS-551AVT

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### 7. Test information

#### 7.1 Ruggedness in Doherty operation

The BLC10G27XS-551AVT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 32 V;  $I_{Dq}$  = 1000 mA;  $V_{GS(amp)peak}$  = 0.885 V; f = 2620 MHz;  $P_{L}$  = 230 W (5 dB OBO); 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on the CCDF.

### 7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dq} = 900$  mA (main);  $V_{DS} = 32$  V; pulsed CW ( $t_p = 100 \ \mu s$ ;  $\delta = 10 \ \%$ ).

| f       | Z <sub>S</sub> [1]  | Z <sub>L</sub> [1]  | P <sub>L</sub> [2] | η <sub>D</sub> [2] | G <sub>p</sub> [2] |  |  |
|---------|---------------------|---------------------|--------------------|--------------------|--------------------|--|--|
| (MHz)   | <b>(</b> Ω <b>)</b> | <b>(</b> Ω <b>)</b> | (W)                | (%)                | (dB)               |  |  |
| Maximum | Maximum power load  |                     |                    |                    |                    |  |  |
| 2500    | 1.1 – j5.2          | 1.8 – j4.4          | 306                | 59.3               | 13.9               |  |  |
| 2600    | 1.6 – j5.8          | 1.9 – j4.5          | 301                | 60.0               | 14.1               |  |  |
| 2690    | 2.5 – j6.5          | 2.0 - j4.3          | 298                | 60.2               | 14.2               |  |  |
| Maximum | drain efficiency    | load                |                    |                    |                    |  |  |
| 2500    | 1.2 – j5.4          | 3.9 – j4.5          | 223                | 66.7               | 15.7               |  |  |
| 2600    | 1.7 – j6.0          | 3.8 – j3.3          | 213                | 66.4               | 15.9               |  |  |
| 2690    | 2.8 – j6.6          | 3.1 – j3.0          | 218                | 66.1               | 15.8               |  |  |

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

Table 10. Typical impedance of peak device

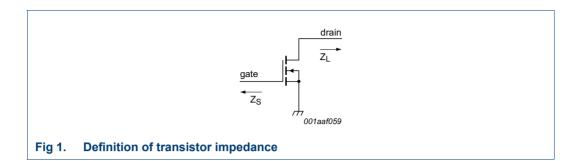
Measured load-pull data of peak device;  $I_{Dq}$  = 1900 mA (peak);  $V_{DS}$  = 32 V; pulsed CW ( $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %).

| f       | Z <sub>S</sub> [1] | Z <sub>L</sub> [1] | P <sub>L</sub> [2] | η <sub>D</sub> [2] | G <sub>p</sub> [2] |
|---------|--------------------|--------------------|--------------------|--------------------|--------------------|
| (MHz)   | <b>(Ω)</b>         | (Ω)                | (W)                | (%)                | (dB)               |
| Maximum | n power load       |                    |                    |                    |                    |
| 2500    | 1.1 – j5.5         | 2.9 – j4.8         | 560                | 56.8               | 12.7               |
| 2600    | 1.5 – j6.3         | 2.9 – j4.3         | 553                | 57.2               | 13.0               |
| 2690    | 2.5 – j7.3         | 2.7 – j4.2         | 544                | 55.7               | 13.0               |
| Maximum | n drain efficiency | load               |                    |                    |                    |
| 2500    | 1.0 – j5.5         | 4.1 – j3.0         | 469                | 56.7               | 14.0               |
| 2600    | 1.6 – j6.3         | 3.4 – j2.4         | 447                | 56.5               | 14.1               |
| 2690    | 2.6 – j7.4         | 2.6 – j2.6         | 442                | 56.5               | 14.2               |

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

<sup>[2]</sup> At 3 dB gain compression.

<sup>[2]</sup> At 3 dB gain compression.



#### 7.3 Test circuit

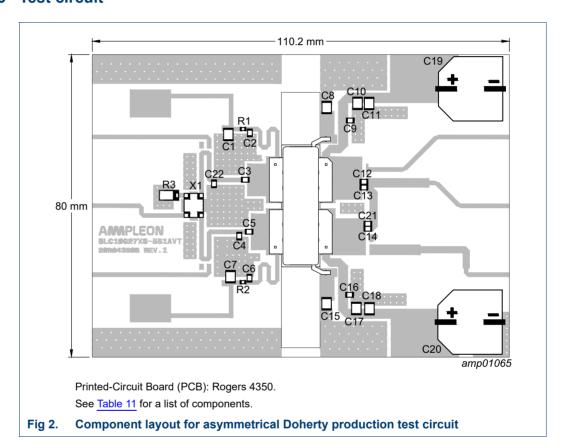


Table 11. List of components

For test circuit see Figure 2.

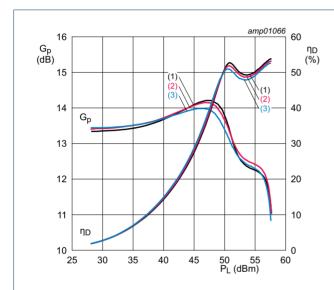
| Component                              | Description                       | Value        | Remarks          |
|--|-----------------------------------|--------------|------------------|
| C1, C7, C8, C10, C11,<br>C15, C17, C18 | multilayer ceramic chip capacitor | 10 μF, 100 V | Murata: 1210     |
| C2, C3, C5, C6, C9, C16                | multilayer ceramic chip capacitor | 6.8 pF       | Murata: HiQ 0805 |
| C4                                     | multilayer ceramic chip capacitor | 0.2 pF       | ATC 800A/8800B   |
| C14, C21                               | multilayer ceramic chip capacitor | 2.7 pF       | Murata: HiQ 0805 |
| C22                                    | multilayer ceramic chip capacitor | 0.3 pF       | ATC 800A/8800B   |
| C12, C13                               | multilayer ceramic chip capacitor | 3.6 pF       | Murata: HiQ 0805 |
| C19, C20                               | multilayer ceramic chip capacitor | 470 μF, 63 V | EEVFK1J471M      |

**Table 11.** List of components ...continued For test circuit see Figure 2.

| Component | Description    | Value      | Remarks                            |
|-----------|----------------|------------|------------------------------------|
| R1, R2    | resistor       | 4.7 Ω, 1 % | SMD 0805                           |
| R3        | resistor       | 50 Ω, 16 W | Anaren: C16A50Z4                   |
| X1        | hybrid coupler |            | Anaren: Xinger III,<br>X3C25P1-02S |

### 7.4 Graphical data

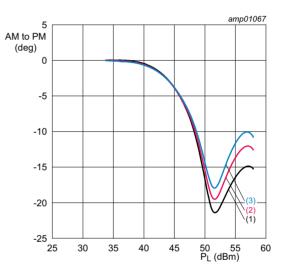
#### 7.4.1 Pulsed CW



 $V_{DS}$  = 32 V;  $I_{Dq}$  = 1000 mA;  $V_{GS(amp)peak}$  = 0.885 V;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values



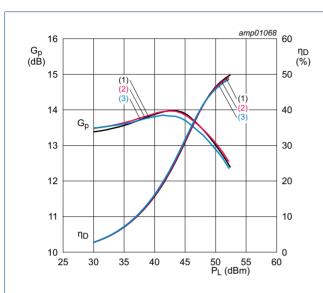
 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 4. Normalized AM to PM as a function of output power; typical values

#### 7.4.2 1-Carrier W-CDMA

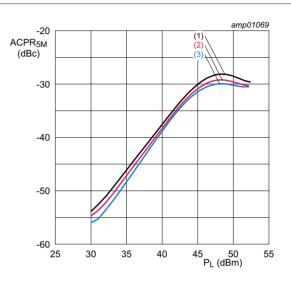
Test signal: 3GPP test model 1; 1 to 64 DPCH (100 % clipping); PAR = 9.9 dB at 0.01 % probability on CCDF per carrier.



 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

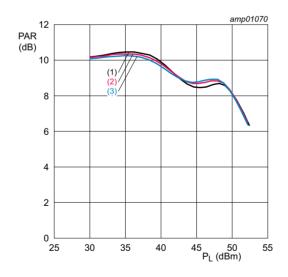
Fig 5. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 6. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



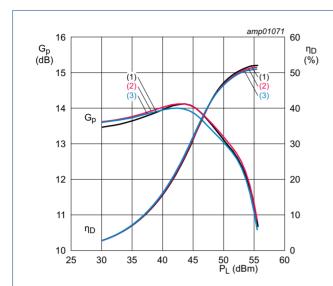
 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 7. Peak-to-average power ratio as a function of output power; typical values

#### 7.4.3 1-Carrier LTE

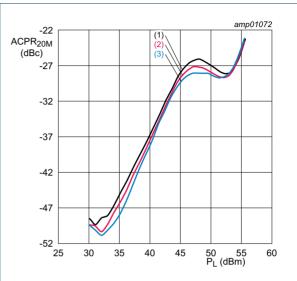
Test signal: 1-carrier LTE 10 MHz; PAR = 6.8 dB at 0.01 % probability on CCDF.



 $V_{DS} = 32 \text{ V}; I_{Dq} = 1000 \text{ mA}; V_{GS(amp)peak} = 0.885 \text{ V}.$ 

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

Fig 8. Power gain and drain efficiency as function of output power; typical values

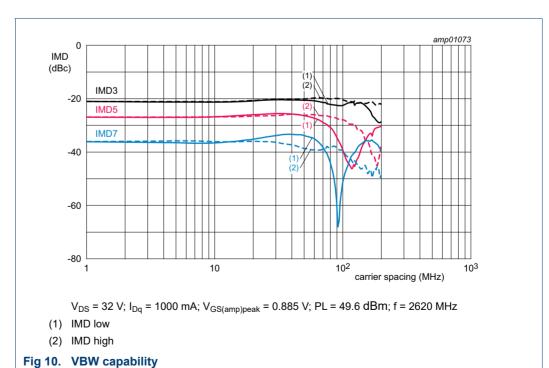


 $V_{DS} = 32 \text{ V}$ ;  $I_{Dq} = 1000 \text{ mA}$ ;  $V_{GS(amp)peak} = 0.885 \text{ V}$ .

- (1) f = 2620 MHz
- (2) f = 2655 MHz
- (3) f = 2690 MHz

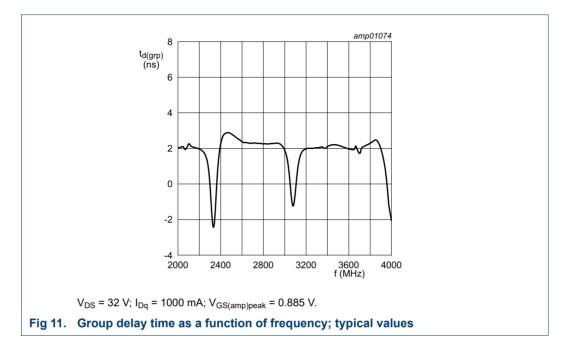
Fig 9. Adjacent channel power ratio (20 MHz) as a function of output power; typical values

#### 7.4.4 2-Tone VBW



BLC10G27XS-551AVT

#### 7.4.5 Group delay



# 8. Package outline

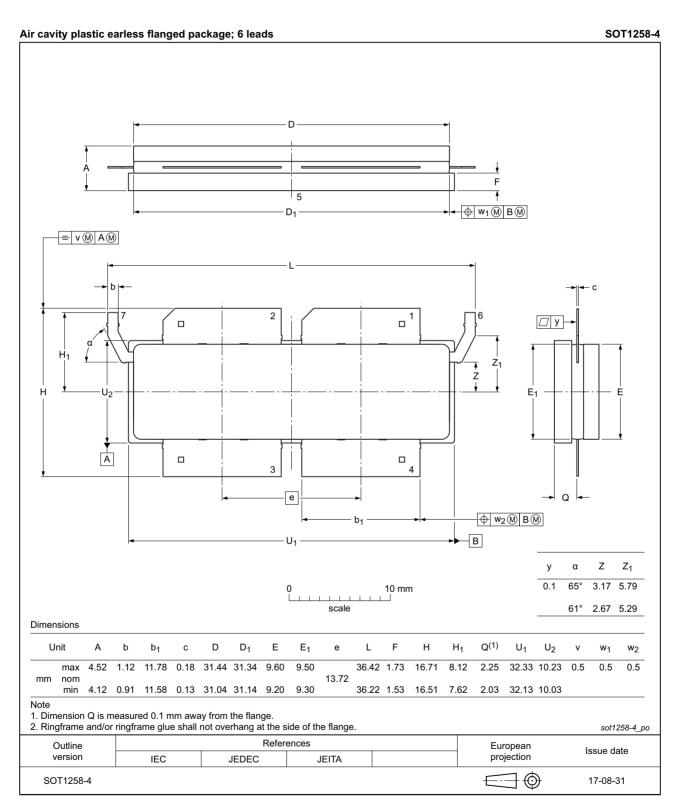


Fig 12. Package outline SOT1258-4

# 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12. ESD sensitivity

| ESD model  | Class  |
|--|--------|
| Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002 | C3 [1] |
| Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001     | 2 [2]  |

- [1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of 1000 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

#### 10. Abbreviations

Table 13. Abbreviations

| Acronym | Description                                    |  |  |
|---------|--|--|--|
| 3GPP    | 3rd Generation Partnership Project             |  |  |
| AM      | Amplitude Modulation                           |  |  |
| CCDF    | Complementary Cumulative Distribution Function |  |  |
| CW      | Continuous Wave                                |  |  |
| DPCH    | Dedicated Physical CHannel                     |  |  |
| ESD     | ElectroStatic Discharge                        |  |  |
| LDMOS   | Laterally Diffused Metal-Oxide Semiconductor   |  |  |
| LTE     | Long Term Evolution                            |  |  |
| MTF     | Median Time to Failure                         |  |  |
| ОВО     | Output Back Off                                |  |  |
| PAR     | Peak-to-Average Ratio                          |  |  |
| PM      | Phase Modulation                               |  |  |
| RoHS    | Restriction of Hazardous Substances            |  |  |
| SMD     | Surface Mounted Device                         |  |  |
| VBW     | Video BandWidth                                |  |  |
| VSWR    | Voltage Standing Wave Ratio                    |  |  |
| W-CDMA  | Wideband Code Division Multiple Access         |  |  |

# 11. Revision history

Table 14. Revision history

| Document ID           | Release date | Data sheet status  | Change notice | Supersedes |
|-----------------------|--------------|--------------------|---------------|------------|
| BLC10G27XS-551AVT v.1 | 20190920     | Product data sheet | -             | -          |

BLC10G27XS-551AVT

## 12. Legal information

#### 12.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

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- [2] The term 'short data sheet' is explained in section "Definitions"
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#### **Power LDMOS transistor**

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#### 13. Contact information

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### 14. Contents

| 1     | Product profile                   |
|-------|-----------------------------------|
| 1.1   | General description               |
| 1.2   | Features and benefits             |
| 1.3   | Applications                      |
| 2     | Pinning information 2             |
| 3     | Ordering information              |
| 4     | Limiting values                   |
| 5     | Thermal characteristics 2         |
| 6     | Characteristics                   |
| 7     | Test information 4                |
| 7.1   | Ruggedness in Doherty operation 4 |
| 7.2   | Impedance information 4           |
| 7.3   | Test circuit5                     |
| 7.4   | Graphical data 6                  |
| 7.4.1 | Pulsed CW 6                       |
| 7.4.2 | 1-Carrier W-CDMA                  |
| 7.4.3 | 1-Carrier LTE                     |
| 7.4.4 | 2-Tone VBW                        |
| 7.4.5 | Group delay                       |
| 8     | Package outline                   |
| 9     | Handling information11            |
| 10    | Abbreviations11                   |
| 11    | Revision history                  |
| 12    | Legal information                 |
| 12.1  | Data sheet status                 |
| 12.2  | Definitions                       |
| 12.3  | Disclaimers                       |
| 12.4  | Trademarks                        |
| 13    | Contact information               |
| 14    | Contents                          |

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